

L Number	Hits	Search Text	DB	Time stamp
1	49	electric adj arc same source near4 vapor\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2003/03/09 16:08
10	7	("3101308" "5207999" "5211995" "5227038" "5318628" "5344889" "5573732").PN.		2003/03/09 16:17
-	16	(sic or silicon adj carbide) near3 electrode and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:11
-	14	(sic or silicon adj carbide) and electric\$4 near3 arc and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:32
-	2	electric\$4 near3 arc same (silicon adj carbide or sic) same (sublim\$4 or sublimat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:36
-	4	electric\$4 near3 arc same (silicon adj carbide or sic) near4 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:47
-	73	(silicon adj carbide or sic) near2 electrode same (vapor\$4 or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:52
-	23	(silicon adj carbide or sic) near2 electrode near5 (vapor\$4 or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:54
-	3	(silicon adj carbide or sic) near2 electrode near5 (vapor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:55
-	1	6514338.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:56
-	2	yano.in. and (sic or silicon adj carbide) and arc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 15:59
-	3	yano.in. and (sic or silicon adj carbide) near3 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:07
-	13	(sic or silicon adj carbide) near3 electrode and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:04
-	99	(sic or silicon adj carbide) near3 sublim\$5 and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:17

-	0	(sic or silicon adj carbide) near3 sublim\$5 same electric\$3 near2 arc and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:05
-	30	(sic or silicon adj carbide) near3 sublim\$5 near4 source and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:19
-	22	(sic or silicon adj carbide) and coleman.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:21
-	4	(silicon adj carbide or sic) near3 electrode same electric\$4 near2 arc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:23
-	23	(silicon adj carbide or sic) near3 electrode and electric\$4 near2 arc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/24 16:24
-	9	4505948.URPN. and electrode	USPAT	2003/03/06 17:07
-	42	(sic or silicon adj carbide) near3 seed same sublimat\$4	USPAT	2003/03/06 17:09
-	70	(sic or silicon adj carbide) same sublimat\$4 and electrode	USPAT	2003/03/06 17:10
-	19	(sic or silicon adj carbide) same sublimat\$4 and electrode near4 (sic or silicon adj carbide)	USPAT	2003/03/06 17:14
-	40	(sic or silicon adj carbide) same sublimat\$4 and arc	USPAT	2003/03/06 17:16
-	83	(sic or silicon adj carbide) same arc near3 electric\$4	USPAT	2003/03/07 10:24
-	49	(sic or silicon adj carbide) near4 seed and (silicon adj carbide or sic) same (sublimat\$4) and 117\$5.ccls.	USPAT	2003/03/07 10:34
-	33	electric\$4 near2 arc same sublimat\$4	USPAT	2003/03/07 10:44
-	32	electric\$4 near2 arc and 117\$4.ccls.	USPAT	2003/03/07 11:07
-	22	pinkhasov.in.	USPAT	2003/03/07 16:44
-	41	sinter\$4 near4 carbide near3 silicon same electrode	USPAT	2003/03/07 11:34
-	56	sinter\$4 near4 carbide near3 silicon and type near2 powder	USPAT	2003/03/07 11:35
-	1	sinter\$4 near4 carbide near3 silicon and type near2 powder near2 (n or p)	USPAT	2003/03/07 11:41
-	14	sinter\$4 near4 carbide near3 silicon and p\$type	USPAT	2003/03/07 13:33
-	56	single adj crystal\$4 near3 (sic or silicon adj carbide) and (sic or silicon adj carbide) near2 seed and sublimat\$4	USPAT	2003/03/07 13:56
-	3	electric adj arc and ac! near4 power same dc and sublimat\$4	USPAT	2003/03/07 14:39
-	43	electric adj arc and ac! near4 power same dc same frequency	USPAT	2003/03/07 14:42
-	1	electric adj arc and ac! near4 power same dc same frequency near3 constant\$4	USPAT	2003/03/07 14:44
-	4	electric adj arc and ac! same frequency near3 constant\$4	USPAT	2003/03/07 14:45
-	63	electric adj arc same mov\$4 same constant\$4	USPAT	2003/03/07 15:14
-	35	electric adj arc same mov\$4 same constant\$4 same electrode	USPAT	2003/03/07 15:36

-	3	(silicon adj carbide or sic) near4 seed near6 rotat\$5 and sublimat\$4	USPAT	2003/03/07 15:38
-	14	(silicon adj carbide or sic) near4 seed and sublimat\$4 and seed near4 rotat\$4	USPAT	2003/03/07 15:41
-	21	pinkhasov.in. and electrode	USPAT	2003/03/07 16:45
-	11	pinkhasov.in. and electrode same carbide	USPAT	2003/03/07 16:49
-	37	electrode near5 (silicon adj carbide or sic) and electric\$4 adj arc	USPAT	2003/03/07 16:59
-	11	arc near5 vapor near4 deposit\$4 same (silicon adj carbide or sic)	USPAT	2003/03/07 17:07
-	74	arc near5 vapor near4 deposit\$4 and (silicon adj carbide or sic)	USPAT	2003/03/07 17:08
-	8	arc near5 vapor near4 deposit\$4 and (silicon adj carbide or sic) near5 electrode	USPAT	2003/03/08 15:03
-	32	seed and (silicon adj carbide or sic) same lely	USPAT	2003/03/07 17:39
-	23	seed near4 (silicon or si) and (silicon adj carbide or sic) same lely	USPAT	2003/03/07 17:41
-	77	constant near4 gap and electric\$4 adj arc	USPAT	2003/03/08 16:49
-	37	constant near4 gap same electrode and electric\$4 adj arc	USPAT	2003/03/08 17:15
-	2	silicon adj carbide same sublimation and constant adj pressure	USPAT	2003/03/08 17:39
-	15	(sic or silicon adj carbide) near4 sublimat\$4 and heater same source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 17:43
-	71	electric adj arc near10 (ac) near5 dc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/09 16:07